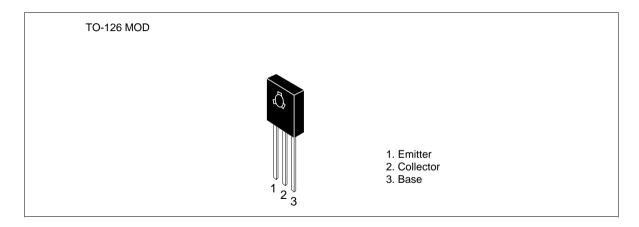
Silicon NPN Epitaxial

HITACHI

Application

Low frequency power amplifier complementary pair with 2SB649/A

Outline





Absolute Maximum Ratings (Ta = 25°C)

		Ratings			
Item	Symbol	2SD669	2SD669A	Unit	
Collector to base voltage	V_{CBO}	180	180	V	
Collector to emitter voltage	V_{CEO}	120	160	V	
Emitter to base voltage	V_{EBO}	5	5	V	
Collector current	I _c	1.5	1.5	А	
Collector peak current	I _{C(peak)}	3	3	А	
Collector power dissipation	P _c	1	1	W	
	P _c *1	20	20	W	
Junction temperature	Tj	150	150	°C	
Storage temperature	Tstg	-55 to +150	-55 to +150	°C	

Note: 1. Value at $T_c = 25^{\circ}C$.

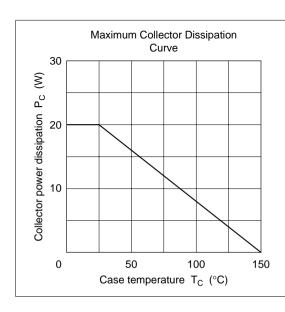
Electrical Characteristics ($Ta = 25^{\circ}C$)

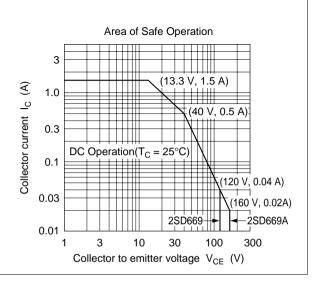
		2SD669A 2SD669A							
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	180	_	_	180	_	_	V	$I_{\rm C} = 1$ mA, $I_{\rm E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	120	_	_	160	_	_	V	$I_{\rm C}$ = 10 mA, $R_{\rm BE}$ = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	5	_	_	V	$I_{E} = 1 \text{ mA}, I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	10	_	_	10	μΑ	V _{CB} = 160 V, I _E = 0
DC current transfer ratio	h _{FE1} *1	60	_	320	60	_	200		$V_{CE} = 5 \text{ V}, I_{C} = 150 \text{ mA}^{*2}$
	h _{FE2}	30	_	_	30	_	_		$V_{CE} = 5 \text{ V}, I_{C} = 500 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1	_	_	1	V	$I_{\rm C} = 500 \text{ mA},$ $I_{\rm B} = 50 \text{ mA}^{*2}$
Base to emitter voltage	V _{BE}	_	_	1.5	_	_	1.5	V	$V_{CE} = 5 \text{ V}, I_{C} = 150 \text{ mA}^{*2}$
Gain bandwidth product	f _T	_	140		_	140	_	MHz	$V_{CE} = 5 \text{ V}, I_{C} = 150 \text{ mA}^{*2}$
Collector output capacitance	Cob	_	14	_	_	14	_	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0,$ f = 1 MHz

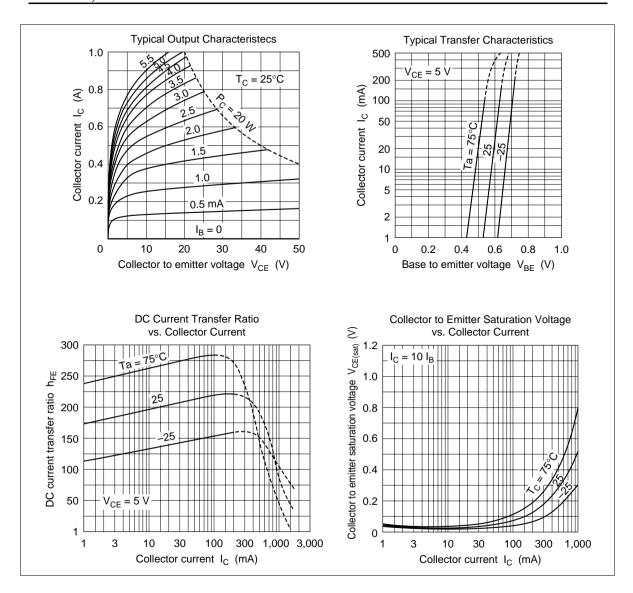
Notes: 1. The 2SD669 and 2SD669A are grouped by h_{FE1} as follows.

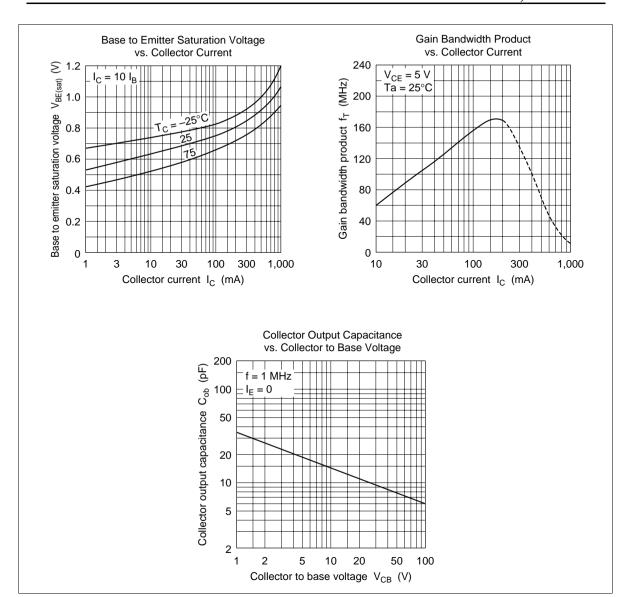
2. Pulse test.

	В	С	D
2SD669	60 to 120	100 to 200	160 to 320
2SD669A	60 to 120	100 to 200	_

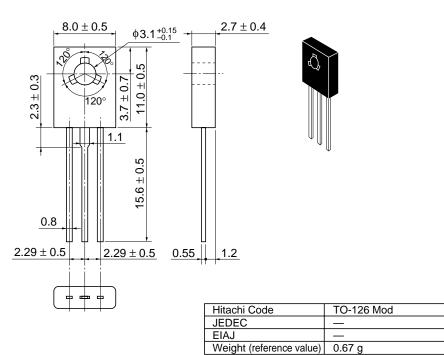








Unit: mm



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